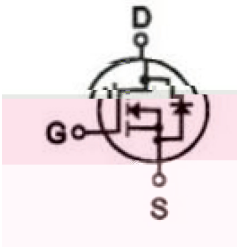
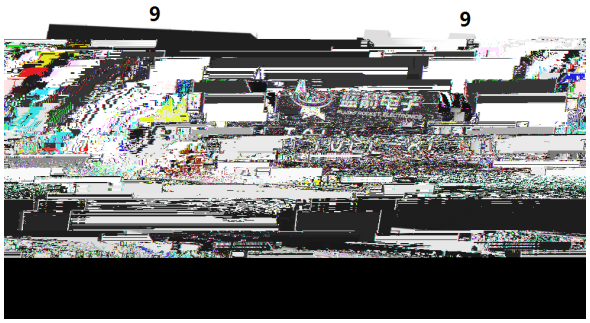
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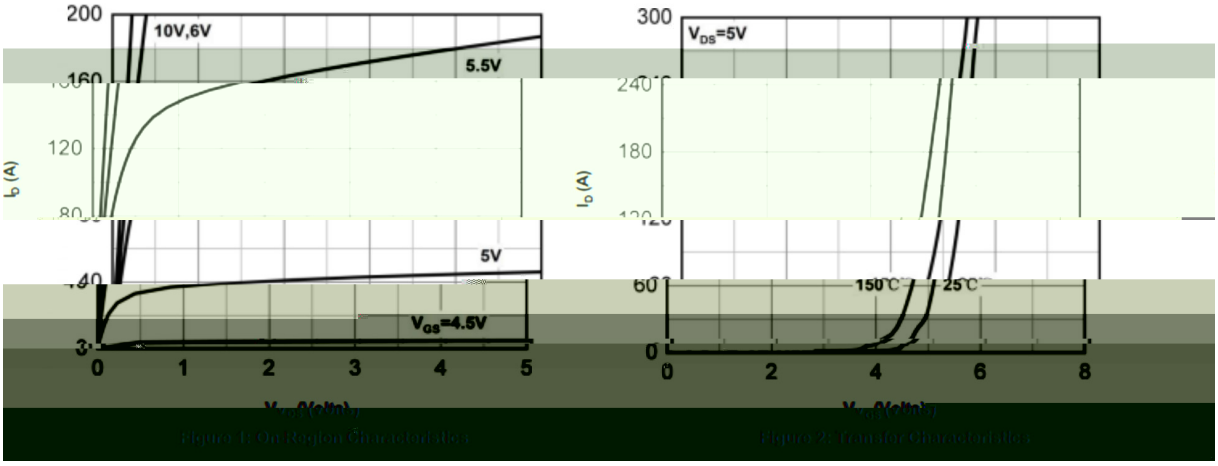


Figure 1: On-Region Characteristics

Figure 2: Transfer Characteristics

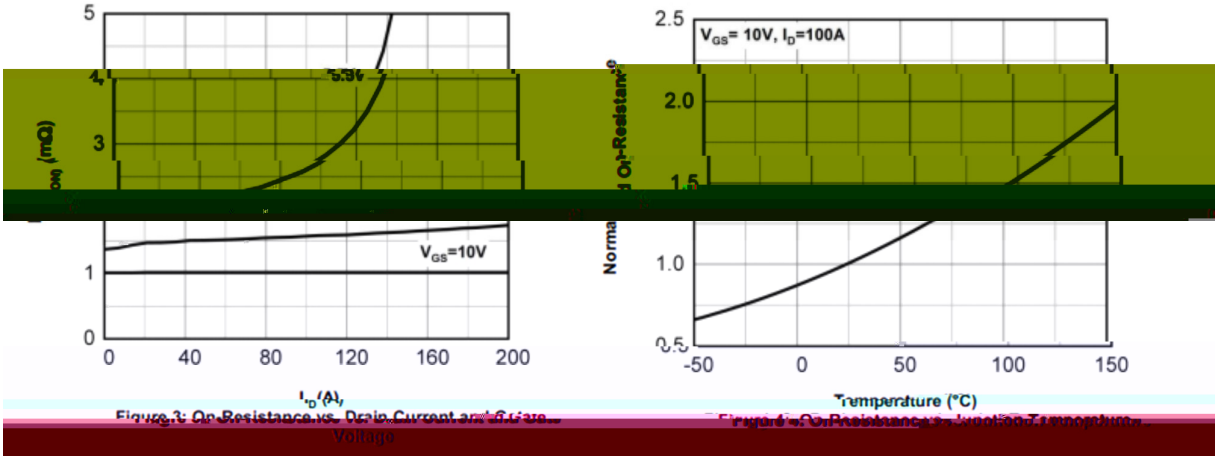


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

Figure 4: On-Resistance vs. Junction Temperature

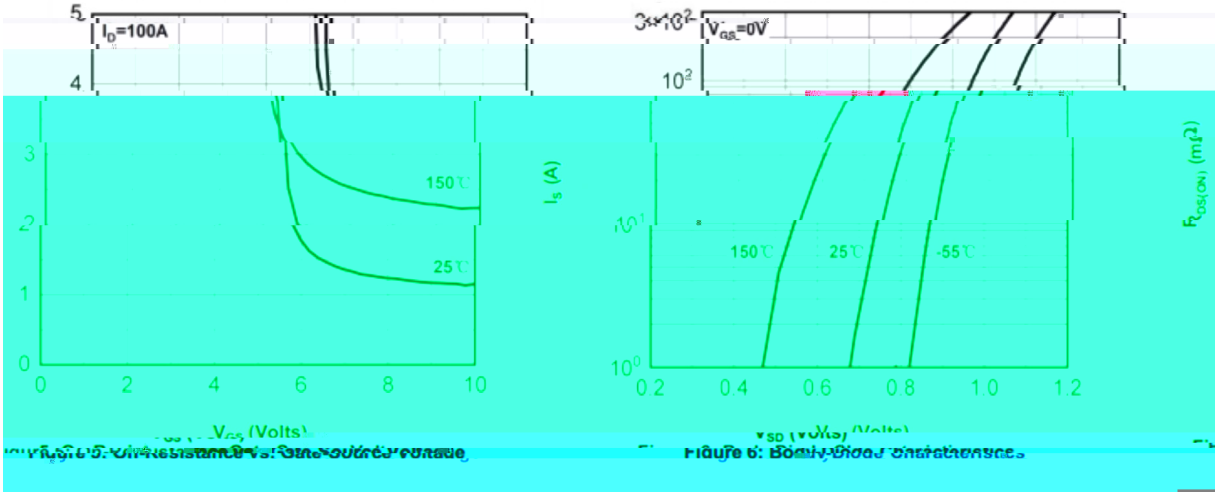
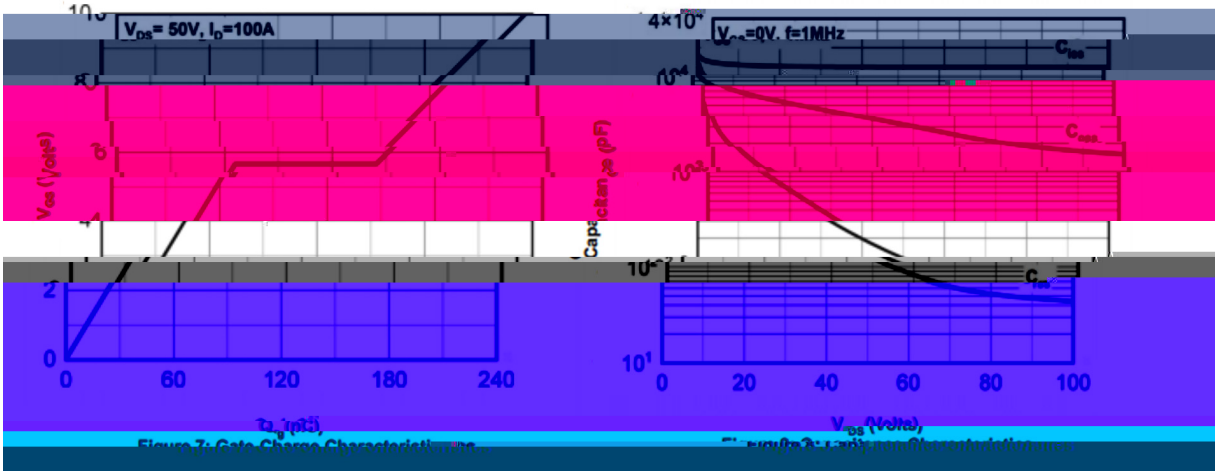
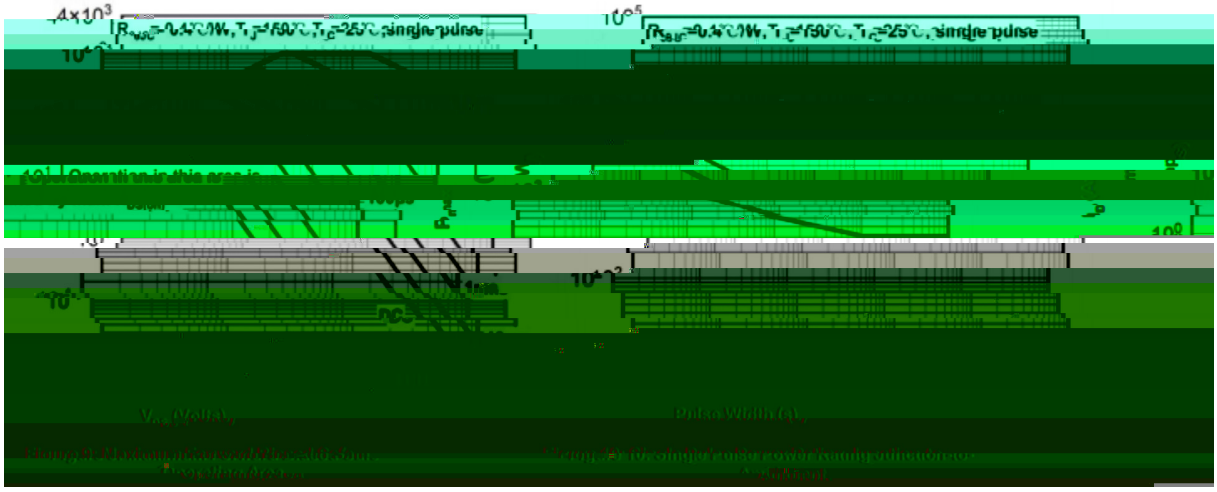
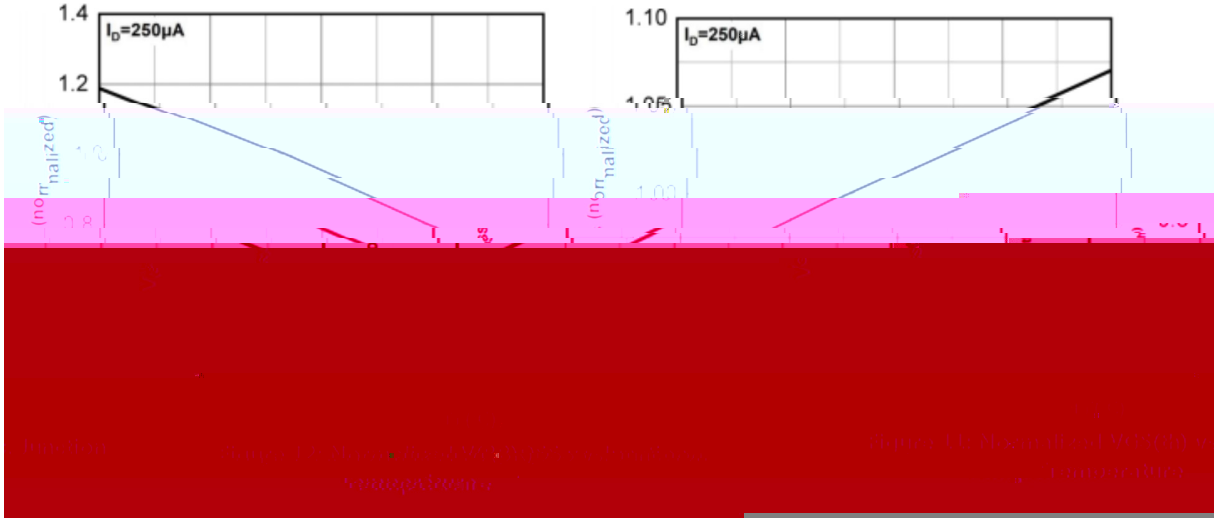


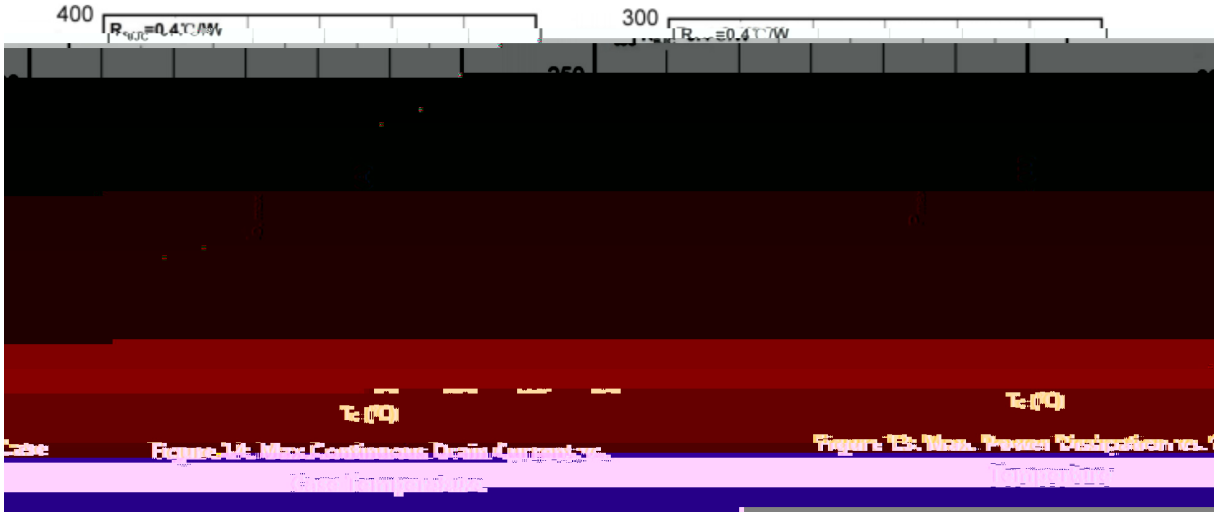
Figure 5: On-Resistance vs. Source-Drain Voltage

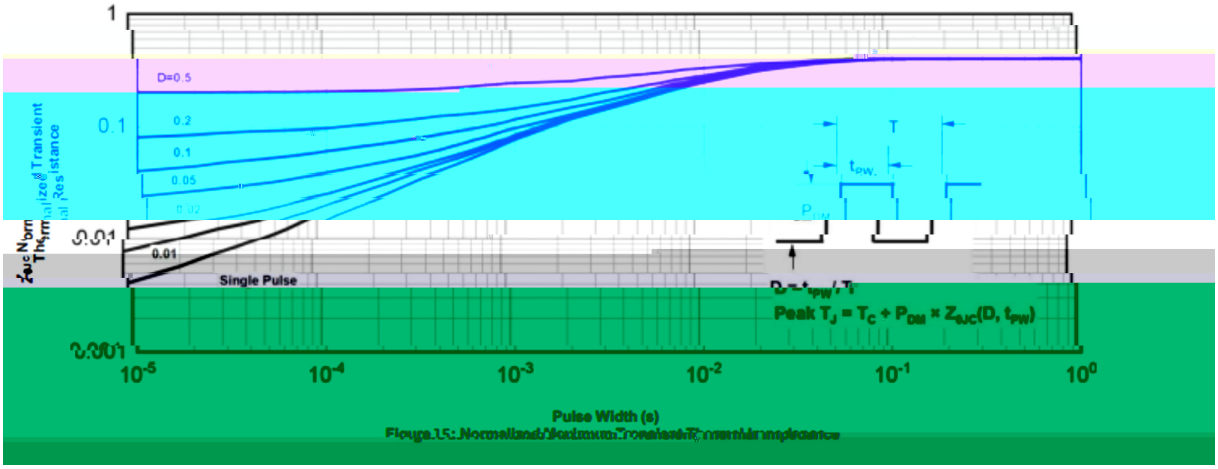
Figure 6: Body-Diode Characteristics


V_DS= 50V, I_D=100A
V_GS (Volts)
Q_g (nC)
0
60
120
180
240
0
2
4
6
8
V_GS=0V, f=1MHz
C_iss
C_oss
C_rss
Capacitance (pF)
0
20
40
60
80
100
V_DS (Volts)


R_θJC=0.47°C/W, T_J=150°C, T_C=25°C, single pulse
R_θJC=0.47°C/W, T_J=150°C, T_C=25°C, single pulse
Pulse Width (s)


I_D=250μA
I_D=250μA
1.4
1.2
1.10
(normalized)


400
300


1
0.1
0.01
0.001
D=0.5
0.2
0.1
0.05
0.02
0.01
Single Pulse
T
t_{PW}
P_{DM}
Peak $T_J = T_C + P_{DM} \times Z_{\theta JC}(D, t_{PW})$
10^{-5}
10^{-4}
10^{-3}
10^{-2}
10^{-1}
10^{0}
Pulse Width (s)

Temperature Profile for IR Reflow Soldering(Pb-Free)

± ± ± ±

± ±